

M Siva Pratap Reddy

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Effect of Temperature on the Electrical and Current Transport Properties of Au/Nd ₂ O ₃ /n-GaN Metal/Interlayer/Semiconductor (MIS) Junction. Applied Physics A: Materials Science and Processing, 2021, 127, 1.	2.3	6
2	Tunable room temperature ferromagnetism and optical bandgap of CdS:Er nanoparticles. Applied Physics A: Materials Science and Processing, 2021, 127, 1.	2.3	1
3	Magnetic, electron paramagnetic resonance, and photocatalytic analysis of diluted magnetic semiconductor CdS:V nanoparticles. Ceramics International, 2021, 47, 16240-16247.	4.8	4
4	Doping-induced photocatalytic activity and hydrogen evolution of ZnS: V nanoparticles. Ceramics International, 2021, 47, 26438-26446.	4.8	16
5	Enhanced photocatalytic activity and hydrogen evolution of CdS nanoparticles through Er doping. Ceramics International, 2020, 46, 21728-21735.	4.8	21
6	Electrical and carrier transport properties of Au/Pr ₆ O ₁₁ /n-GaN MIS structure with a high-k rare-earth oxide interlayer at high temperature range. Vacuum, 2020, 174, 109201.	3.5	12
7	Temperature- and light-sensitive mechanism in metal/organic/n-GaN bio-hybrid temperature photodiode based on salmon DNA biomolecule. Journal of Materials Science: Materials in Electronics, 2019, 30, 11771-11777.	2.2	3
8	Enhanced surface and optical properties of colloidal silver nano-particles on GaN-based light-emitting diodes by a localized surface plasmon resonance effect using a low-cost metal-assisted chemical etching method. Optics Communications, 2019, 450, 276-281.	2.1	15
9	Achieving enhanced ferromagnetism in ZnTbO nanoparticles through Cu co-doping. Ceramics International, 2019, 45, 16347-16352.	4.8	6
10	(Al, Cu) Co-doped ZnS nanoparticles: structural, chemical, optical, and photocatalytic properties. Journal of Materials Science: Materials in Electronics, 2019, 30, 9897-9902.	2.2	16
11	Statistical distribution of barrier heights, current conduction mechanism and voltage-dependent capacitance—frequency characteristics of Au/Fe ₃ O ₄ /n-GaN heterojunction. SN Applied Sciences, 2019, 1, 1.	2.9	1
12	Enhanced fluorescence efficiency and photocatalytic activity of ZnS quantum dots through Ga doping. Ceramics International, 2019, 45, 2289-2294.	4.8	41
13	Terbium-doped ZnS quantum dots: Structural, morphological, optical, photoluminescence, and photocatalytic properties. Ceramics International, 2018, 44, 11724-11729.	4.8	41
14	Residue-and-polymer-free graphene transfer: DNA-CTMA/graphene/GaN bio-hybrid photodiode for light-sensitive applications. Optical Materials, 2018, 76, 302-307.	3.6	18
15	Temperature-dependent electrical characteristics and carrier transport mechanism of p-Cu ₂ ZnSnS ₄ /n-GaN heterojunctions. Applied Physics A: Materials Science and Processing, 2018, 124, 1.	2.3	4
16	Dual-Surface Modification of AlGaIn/GaN HEMTs Using TMAH and Piranha Solutions for Enhancing Current and 1/f-Noise Characteristics. IEEE Journal of the Electron Devices Society, 2018, 6, 791-796.	2.1	10
17	Effect of Eu ³⁺ on the morphology, structural, optical, magnetic, and photocatalytic properties of ZnO nanoparticles. Superlattices and Microstructures, 2018, 123, 154-163.	3.1	33
18	Effect of illumination and frequency dependent series resistance and interface state densities on the electrical properties of DNA-CTMA/p-GaN bio-hybrid Schottky photodiode. Polymer Testing, 2017, 59, 107-112.	4.8	13

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19	Fabrication and electrical characterization of Al/DNA-CTMA/p-type a-Si:H photodiode based on DNA-CTMA biomaterial. <i>Electronic Materials Letters</i> , 2017, 13, 9-15.	2.2	3
20	DNA-CTMA/a-Si:H bio-hybrid photodiode: A light-sensitive photosensor. <i>Organic Electronics</i> , 2017, 50, 435-442.	2.6	9
21	Electrical and interface properties of PdAl/Au metal alloyed ohmic contacts on p-type GaN for high-temperature MEMS devices. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 16903-16909.	2.2	8
22	Modified electrical properties and transport mechanism of Ti/p-InP Schottky structure with a polyvinylpyrrolidone (PVP) polymer interlayer. <i>Journal of Materials Science: Materials in Electronics</i> , 2017, 28, 4847-4855.	2.2	37
23	Temperature-Dependent Electrical Properties and Carrier Transport Mechanisms of TMAH-Treated Ni/Au/Al ₂ O ₃ /GaN MIS Diode. <i>Journal of Electronic Materials</i> , 2016, 45, 5655-5662.	2.2	14
24	Effects of high-k zirconium oxide (ZrO ₂) interlayer on the electrical and transport properties of Au/n-type InP Schottky diode. <i>Thin Solid Films</i> , 2016, 619, 231-238.	1.8	27
25	Electrical properties and carrier transport mechanism in V/p-GaN Schottky diode at high temperature range. <i>Superlattices and Microstructures</i> , 2015, 86, 157-165.	3.1	9
26	Dual detection of ultraviolet and visible lights using a DNA-CTMA/GaN photodiode with electrically different polarity. <i>Optics Express</i> , 2014, 22, 908.	3.4	28
27	Electrical properties and the role of inhomogeneities at the polyvinyl alcohol/n-InP schottky barrier interface. <i>Journal of Applied Polymer Science</i> , 2014, 131, .	2.6	19
28	Electrical characteristics of TMAH-surface treated Ni/Au/Al ₂ O ₃ /GaN MIS Schottky structures. <i>Electronic Materials Letters</i> , 2014, 10, 411-416.	2.2	28
29	Influence of tetramethylammonium hydroxide treatment on the electrical characteristics of Ni/Au/GaN Schottky barrier diode. <i>Materials Chemistry and Physics</i> , 2014, 143, 801-805.	4.0	11
30	Hydrogenated amorphous silicon thin film solar cell with buffer layer of DNA-CTMA biopolymer. <i>Modern Physics Letters B</i> , 2014, 28, 1450107.	1.9	8
31	Electrical properties of Au/n-InP and Au/PVA/n-InP Schottky structures. , 2013, , .		0
32	Frequency dependent series resistance and interface states in Au/bio-organic/n-GaN Schottky structures based on DNA biopolymer. <i>Synthetic Metals</i> , 2013, 185-186, 167-171.	3.9	49
33	Effect of annealing temperature on the electrical properties of Au-Ta ₂ O ₅ /n-GaN metal-insulator-semiconductor (MIS) structure. <i>Applied Physics A: Materials Science and Processing</i> , 2013, 113, 713-722.	2.3	15
34	Annealing effects on electrical, structural, and surface morphological properties of Ir/n-InGaN Schottky structures. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2012, 209, 2027-2033.	1.8	4
35	Electrical transport properties of Au/SiO ₂ /n-GaN MIS structure in a wide temperature range. <i>Current Applied Physics</i> , 2012, 12, 765-772.	2.4	43
36	Effect of annealing temperature on electrical properties of Au/polyvinyl alcohol/n-InP Schottky barrier structure. <i>Thin Solid Films</i> , 2012, 520, 5715-5721.	1.8	34

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37	Electrical characterization of Au/n-GaN metal-insulator-semiconductor and Au/SiO ₂ /n-GaN metal-insulator-semiconductor structures. <i>Journal of Alloys and Compounds</i> , 2011, 509, 8001-8007.	5.5	75
38	Electrical, structural and morphological characteristics of rapidly annealed Ni/Pd Schottky rectifiers on n-type GaN. <i>Surface and Interface Analysis</i> , 2011, 43, 1251-1256.	1.8	4
39	Electrical transport characteristics of Ni/Pd/n-GaN Schottky barrier diodes as a function of temperature. <i>Thin Solid Films</i> , 2011, 519, 3844-3850.	1.8	41
40	Structural and electrical properties of rapidly annealed Ni/Mo Schottky barriers on n-type GaN. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 753-759.	1.8	8
41	Electrical properties and interfacial reactions of rapidly annealed Ni/Ru Schottky rectifiers on n-type GaN. <i>Journal of Alloys and Compounds</i> , 2010, 503, 186-191.	5.5	20